

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
FUJISAKI et al.)
Application Number: To be Assigned)
Filed: Concurrently herewith) Art Unit 2815
For: A SEMICONDUCTOR DEVICE AND)
PROCESS FOR PRODUCING THE SAME)
Attorney Docket No. NITT.0154)

Honorable Assistant Commissioner
for Patents
Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT

The above-referenced application is a divisional of U.S. Serial No. 09/984,632 filed October 30, 2001. It includes the same disclosure as U.S. patent application Serial No. 09/984,632.

It is understood that the listed references will be considered in the examination of the application and that no separate copies of the same prior art are required to be provided since they were previously cited or transmitted in the foregoing prior application, pursuant to 37 CFR § 1.98(d). Form(s) PTO 1449 is enclosed listing references cited by the Examining Attorney and submitted by applicant in the prior applications.

This Information Disclosure Statement is submitted with the above-captioned U.S. divisional application. Accordingly, no fee is due or payable at this time.

The Examiner is requested to acknowledge consideration of the information provided in this paper in accordance with prescribed procedures.

Please charge any additional fees or credit any overpayments in connection with this paper to Deposit Account No. 08-1480.

Respectfully submitted,

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<p>Form PTO 1449</p> <p>U.S. Department of commerce Patent and Trademark Office</p> <p>Information Disclosure Statement by Applicant</p>	ATTY. DOCKET NUMBER	SERIAL NUMBER
	NITT.0154	To be assigned
	APPLICANT	
	FUJISAKI et al.	
FILING DATE	GROUP	
	Concurrently herewith	

U.S. Patent Documents

Foreign Patent Documents

Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)

		Phillip J. Caplan, Edward H. Poindexter, Bruce E. Deal and Reda R. Razouk, "ESR Centers, Interface States, and Oxide Fixed Charge in Thermally Oxidized Silicon Wafers", <i>J. Appl. Phys.</i> 50(9), September 1979, pp. 5847-5854
		F. B. McLean, "A Framework for Understanding Radiation-Induced Interface States in SiO_2 MOS Structures", <i>IEEE Transactions on Nuclear Science</i> , Vol. NS-27, No. 6, December 1980, pp. 1651-1657
EXAMINER		DATE CONSIDERED

Examiner: Initial if citation is considered, whether or not citation is in conformance with MPEP 609; draw a line through citation if not in conformance and not considered. Include a copy of this form with next communication to applicant